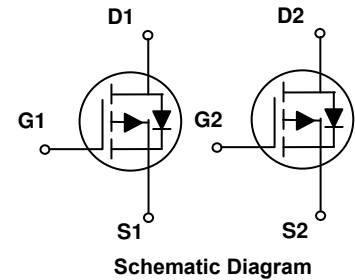
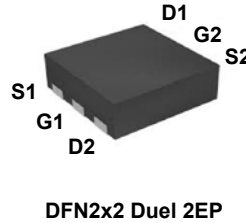


Main Product Characteristics

BV_{DSS}	-20V
$R_{DS(ON)}$	49mΩ
I_D	-4A



Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFB0205 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current–Continuous ($T_A=25^\circ\text{C}$)	I_D	-4	A
Drain Current–Continuous ($T_A=70^\circ\text{C}$)		-3.2	A
Drain Current–Pulsed ¹	I_{DM}	-16	A
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	1.25	W
Power Dissipation–Derate above 25°C		0.01	W/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	100	$^\circ\text{C}/\text{W}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On/Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V, T_J=25^\circ\text{C}$	-	-	-1	μA
		$V_{DS}=-16V, V_{GS}=0V, T_J=125^\circ\text{C}$	-	-	-10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-1.5A$	-	41	49	m Ω
		$V_{GS}=-2.5V, I_D=-1A$	-	54	70	
		$V_{GS}=-1.8V, I_D=-0.8A$	-	76	99	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	-0.4	-0.6	-1	V
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-1A$	-	4	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{2,3}	Q_g	$V_{DS}=-10V, I_D=-2A, V_{GS}=-4.5V$	-	6.4	9	nC
Gate-Source Charge ^{2,3}	Q_{gs}		-	0.9	1.5	
Gate-Drain Charge ^{2,3}	Q_{gd}		-	1.6	3	
Turn-On Delay Time ^{2,3}	$t_{d(on)}$	$V_{DD}=-10V, R_G=6\Omega, V_{GS}=-4.5V, I_D=-2A$	-	5	9	nS
Rise Time ^{2,3}	t_r		-	17.4	33	
Turn-Off Delay Time ^{2,3}	$t_{d(off)}$		-	40.7	80	
Fall Time ^{2,3}	t_f		-	11.4	23	
Input Capacitance	C_{ISS}	$V_{DS}=-10V, V_{GS}=0V, F=1\text{MHz}$	-	540	810	pF
Output Capacitance	C_{OSS}		-	80	120	
Reverse Transfer Capacitance	C_{RSS}		-	75	115	
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	$V_G=V_D=0V, \text{Force Current}$	-	-	-4	A
Pulsed Source Current	I_{SM}		-	-	-8	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	-	-	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

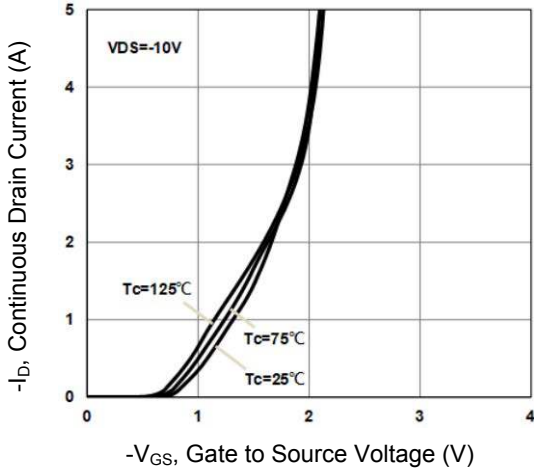


Figure 1. Transfer Characteristics

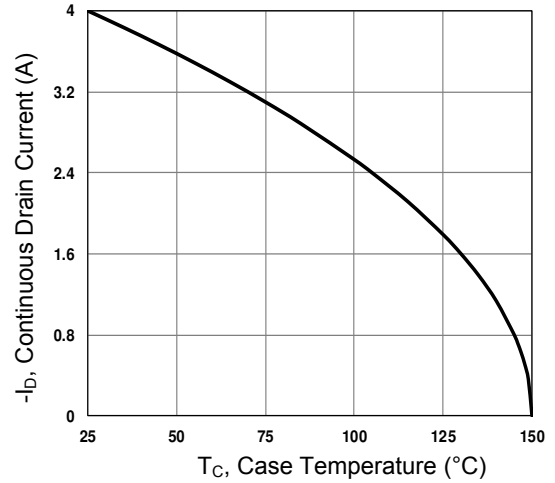


Figure 2. Continuous Drain Current vs. T_C

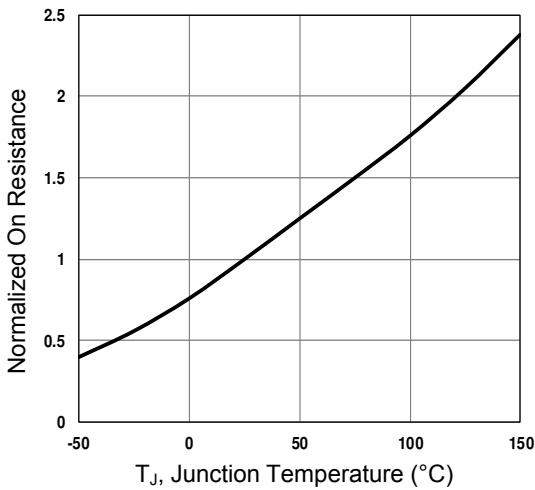


Figure 3. Normalized $R_{DS(ON)}$ vs. T_J

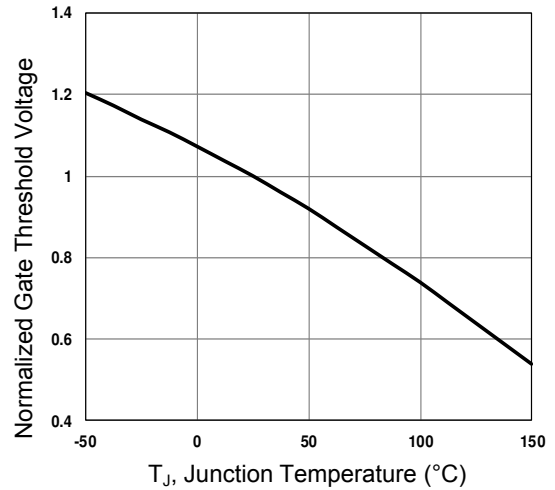


Figure 4. Normalized V_{th} vs. T_J

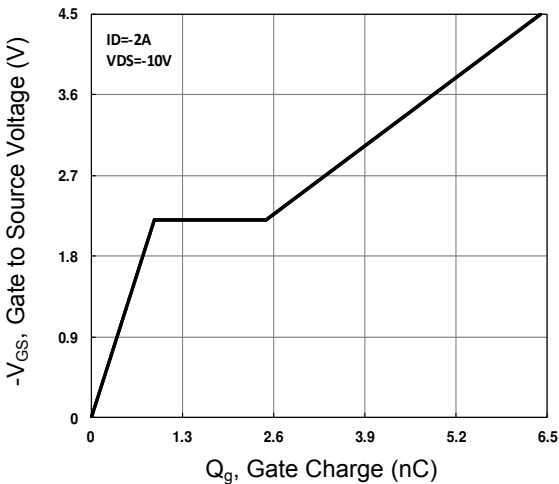


Figure 5. Gate Charge Waveform

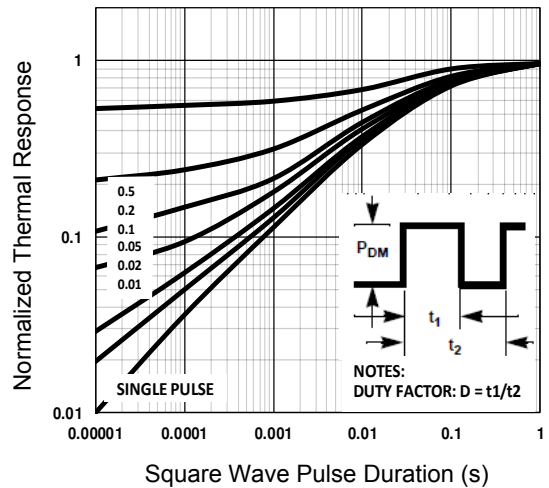


Figure 6. Normalized Transient Impedance

Typical Electrical and Thermal Characteristic Curves

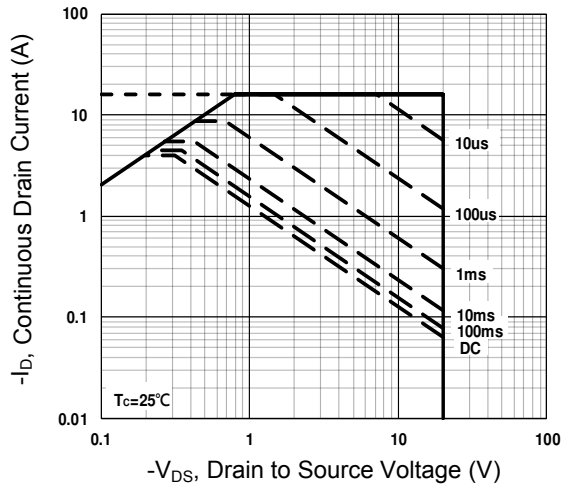
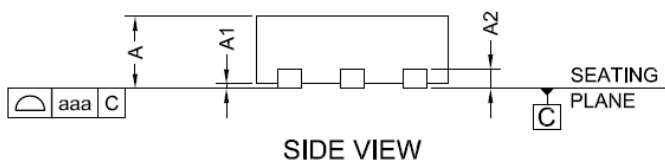
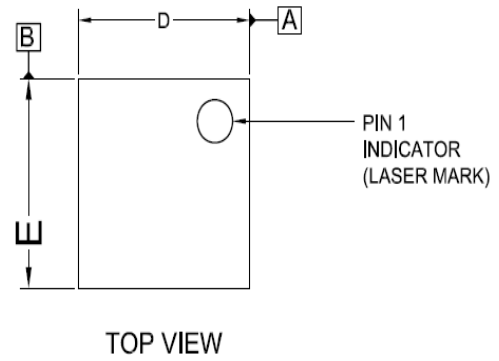
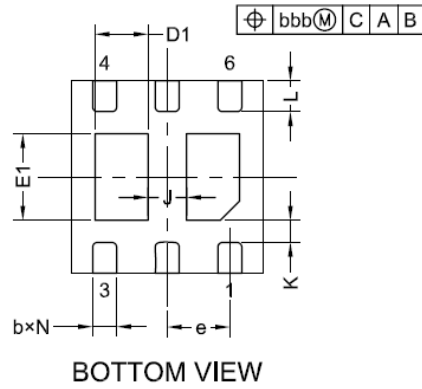


Figure 7. Maximum Safe Operation Area

Package Outline Dimensions (DFN2x2 Duel 2EP)



COMMON DIMENSIONS
 (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2	0.203		
b	0.20	0.25	0.30
D	1.95	2.00	2.05
D1	0.50	0.55	0.60
E	1.95	2.00	2.05
E1	0.85	0.90	0.95
e	0.65BSC		
L	0.27	0.32	0.37
J	0.40BSC		
K	0.20MIN		
N	6		
aaa	0.08		
bbb	0.10		